

HVX-2 Series Power MOSFET

N-Channel Enhancement type

2SK2672
(F5W90HVX2)

900V 5A

FEATURES

- Input capacitance (C_{iss}) is small. Especially, input capacitance at 0 bias is small.
- The static $R_{ds(on)}$ is small.
- The switching time is fast.
- Avalanche resistance guaranteed.

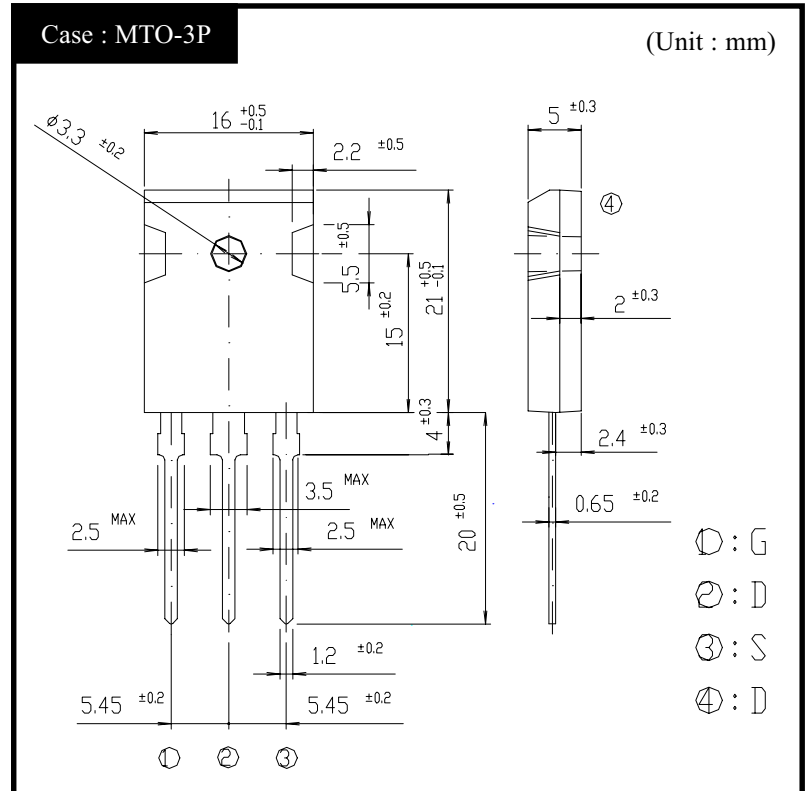
APPLICATION

- Switching power supply of AC 240V input
- High voltage power supply
- Inverter

OUTLINE DIMENSIONS

Case : MTO-3P

(Unit : mm)



RATINGS

●Absolute Maximum Ratings (Tc = 25°C)

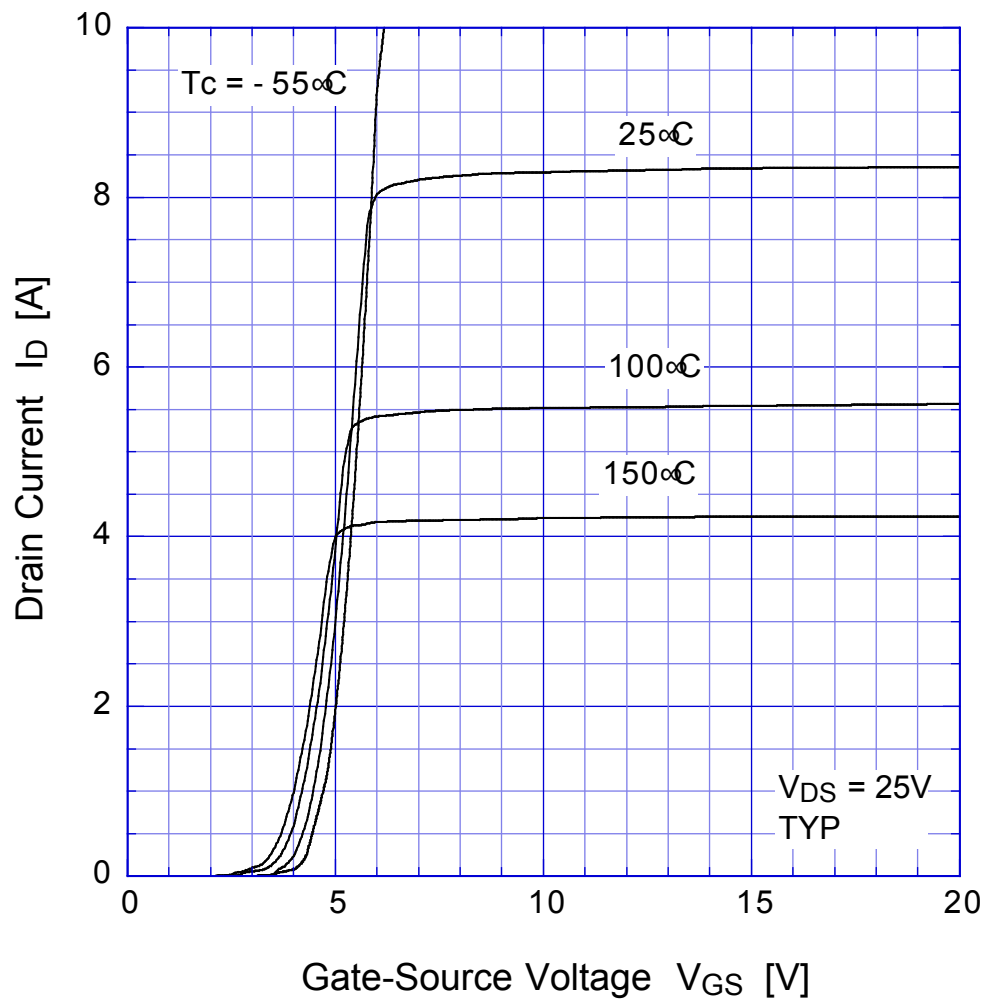
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T _{stg}		-55~150	°C
Channel Temperature	T _{ch}		150	
Drain-Source Voltage	V _{DSS}		900	V
Gate-Source Voltage	V _{GSS}		±30	
Continuous Drain Current(DC)	I _D		5	A
Continuous Drain Current(Peak)	I _{DP}	Pulse width ≤ 10 μs, Duty cycle ≤ 1/100	10	
Continuous Source Current(DC)	I _S		5	
Total Power Dissipation	P _T		80	W
Repetitive Avalanche Current	I _{AR}	T _{ch} = 150°C	5	A
Single Avalanche Energy	E _{AS}	T _{ch} = 25°C	100	mJ
Repetitive Avalanche Energy	E _{AR}	T _{ch} = 25°C	10	
Mounting Torque	TOR	(Recommended torque :0.5 N·m)	0.8	N·m

●Electrical Characteristics $T_c = 25^{\circ}\text{C}$

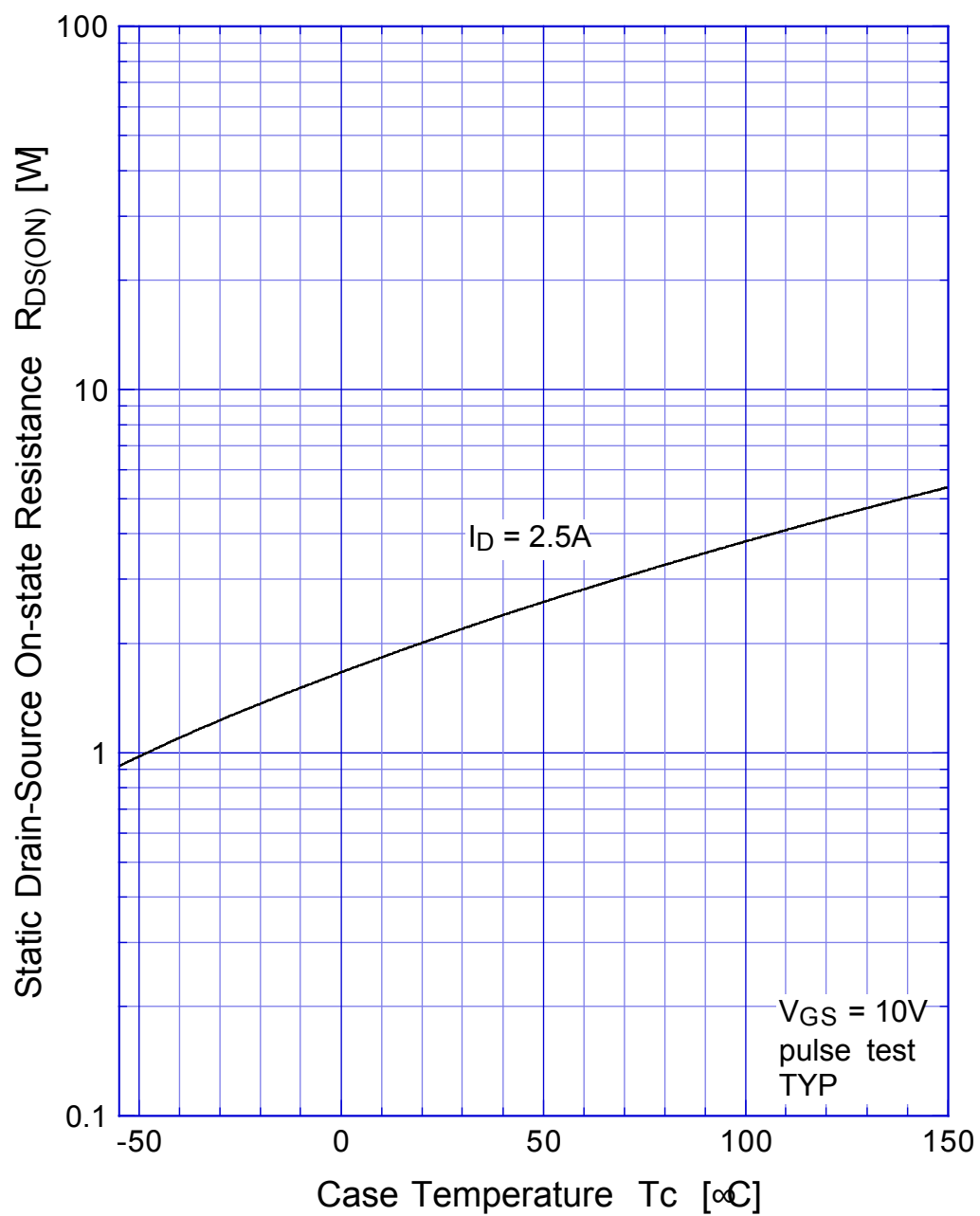
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}$, $V_{GS} = 0\text{V}$	900			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 900\text{V}$, $V_{GS} = 0\text{V}$			250	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$			± 0.1	
Forward Transconductance	g_{fs}	$I_D = 2.5\text{A}$, $V_{DS} = 10\text{V}$	2.4	4.0		S
Static Drain-Source On-state Resistance	$R_{DS(ON)}$	$I_D = 2.5\text{A}$, $V_{GS} = 10\text{V}$		2.1	2.8	Ω
Gate Threshold Voltage	V_{TH}	$I_D = 1\text{mA}$, $V_{DS} = 10\text{V}$	2.5	3.0	3.5	V
Source-Drain Diode Forward Voltage	V_{SD}	$I_S = 2.5\text{A}$, $V_{GS} = 0\text{V}$			1.5	
Thermal Resistance	θ_{jc}	junction to case			1.56	$^{\circ}\text{C}/\text{W}$
Total Gate Charge	Q_g	$V_{DD} = 400\text{V}$, $V_{GS} = 10\text{V}$, $I_D = 5\text{A}$		45		nC
Input Capacitance	C_{iss}	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		1140		pF
Reverse Transfer Capacitance	C_{rss}			23		
Output Capacitance	C_{oss}			105		
Turn-On Time	t_{on}	$I_D = 2.5\text{A}$, $R_L = 60\Omega$, $V_{GS} = 10\text{V}$		55	100	ns
Turn-Off Time	t_{off}			210	350	

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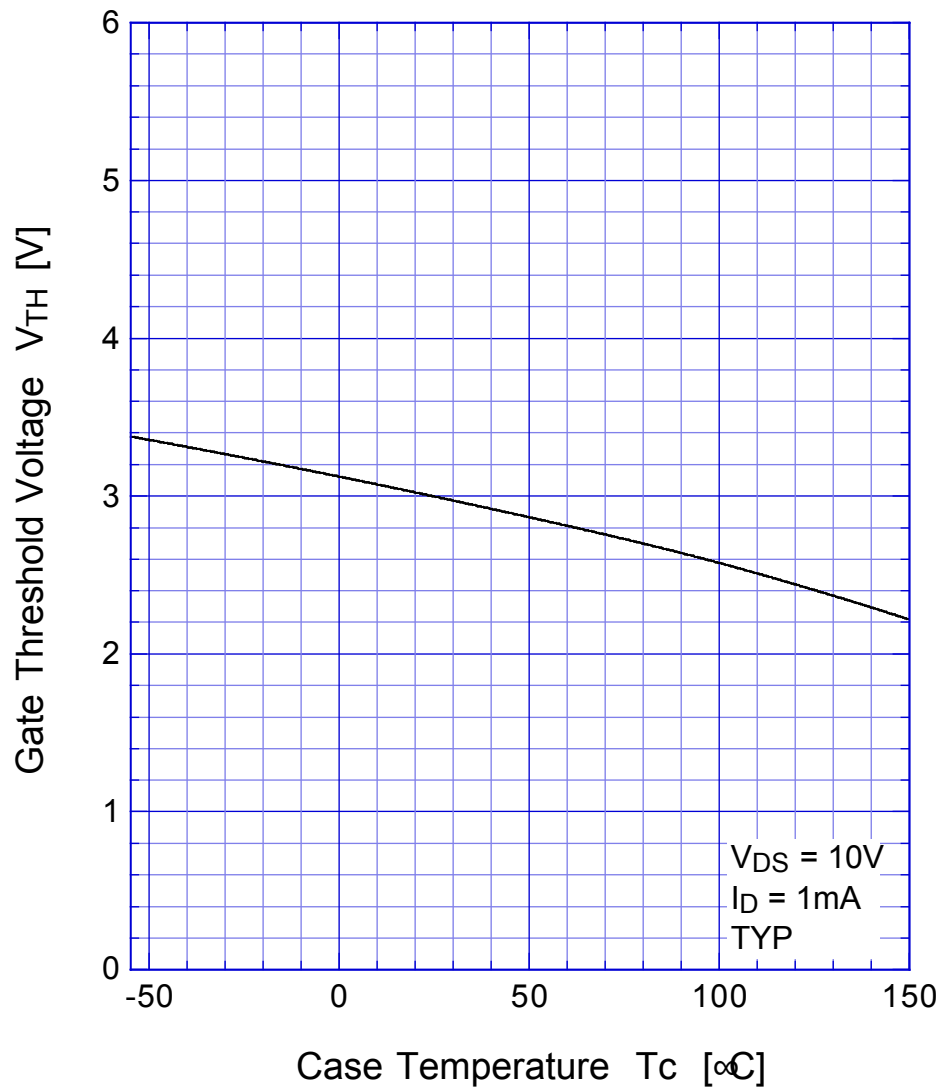
Transfer Characteristics



2SK2672 Static Drain-Source On-state Resistance

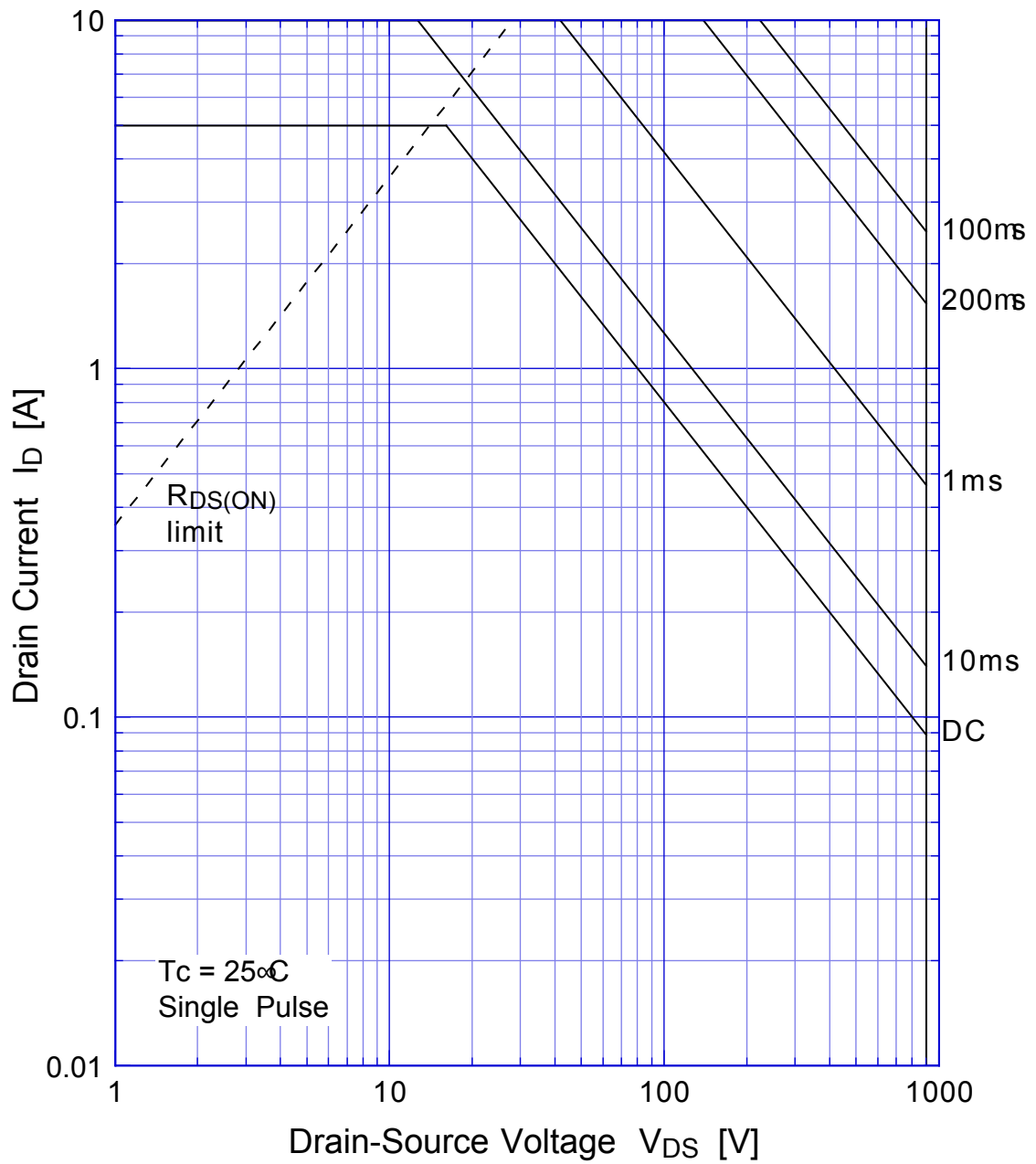


2SK2672 Gate Threshold Voltage

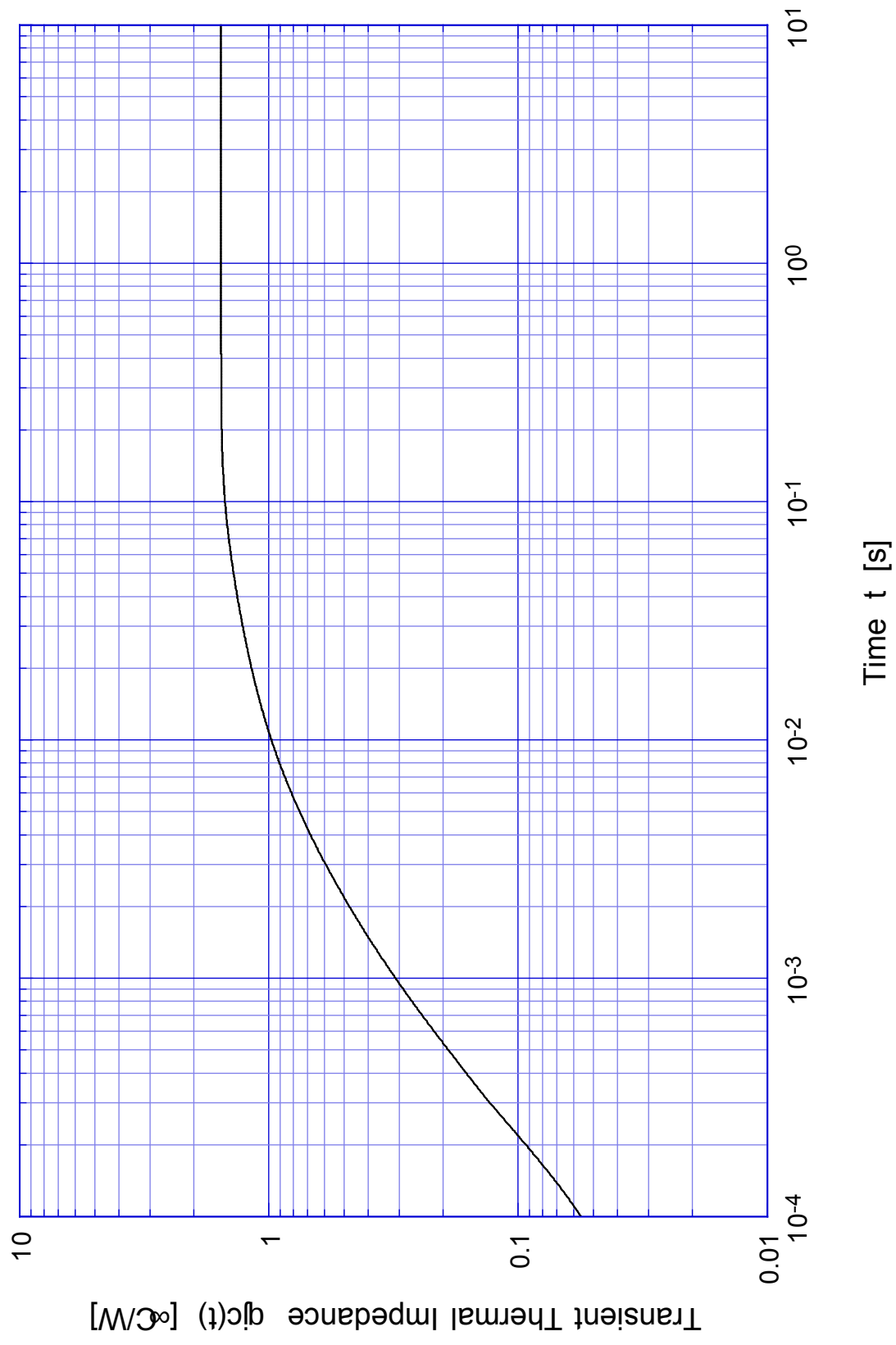


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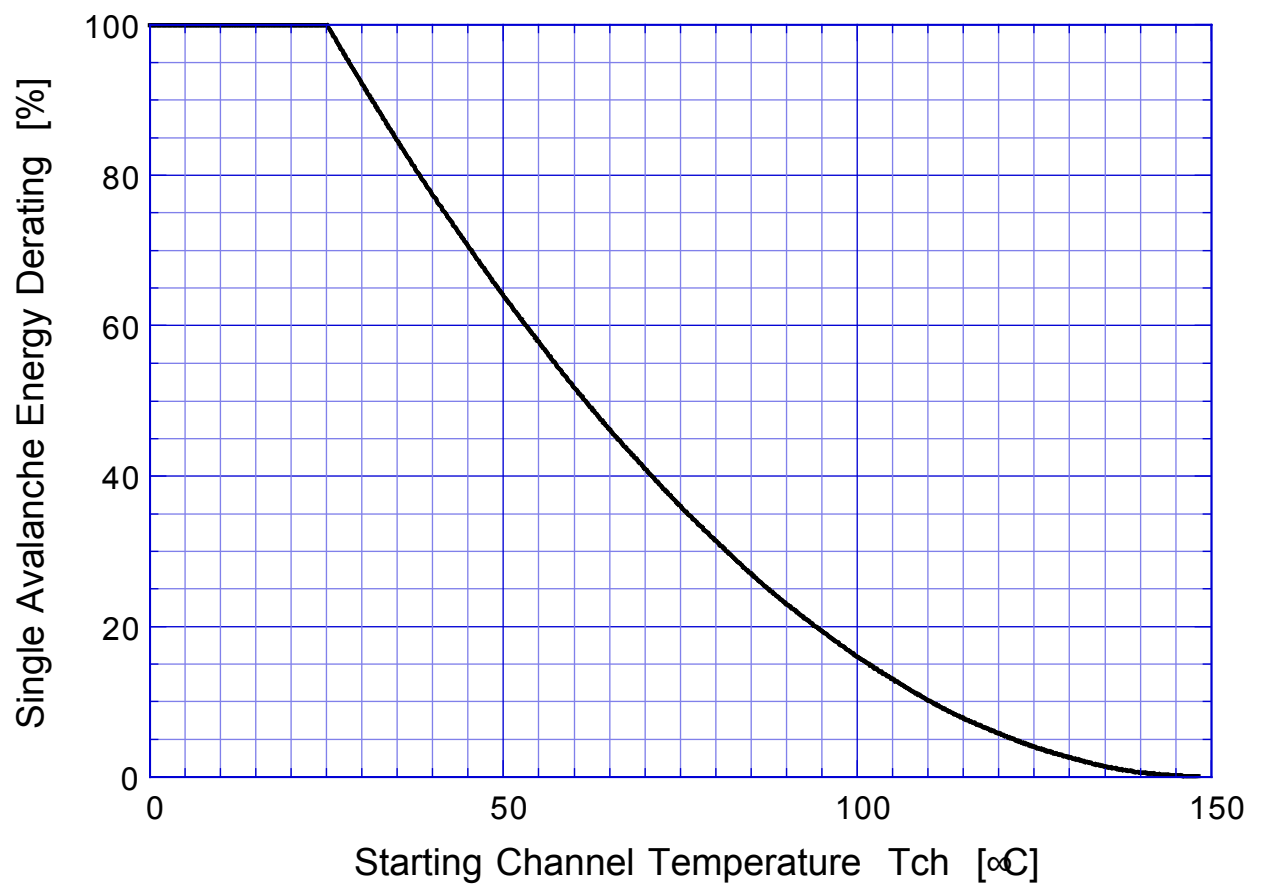
Safe Operating Area



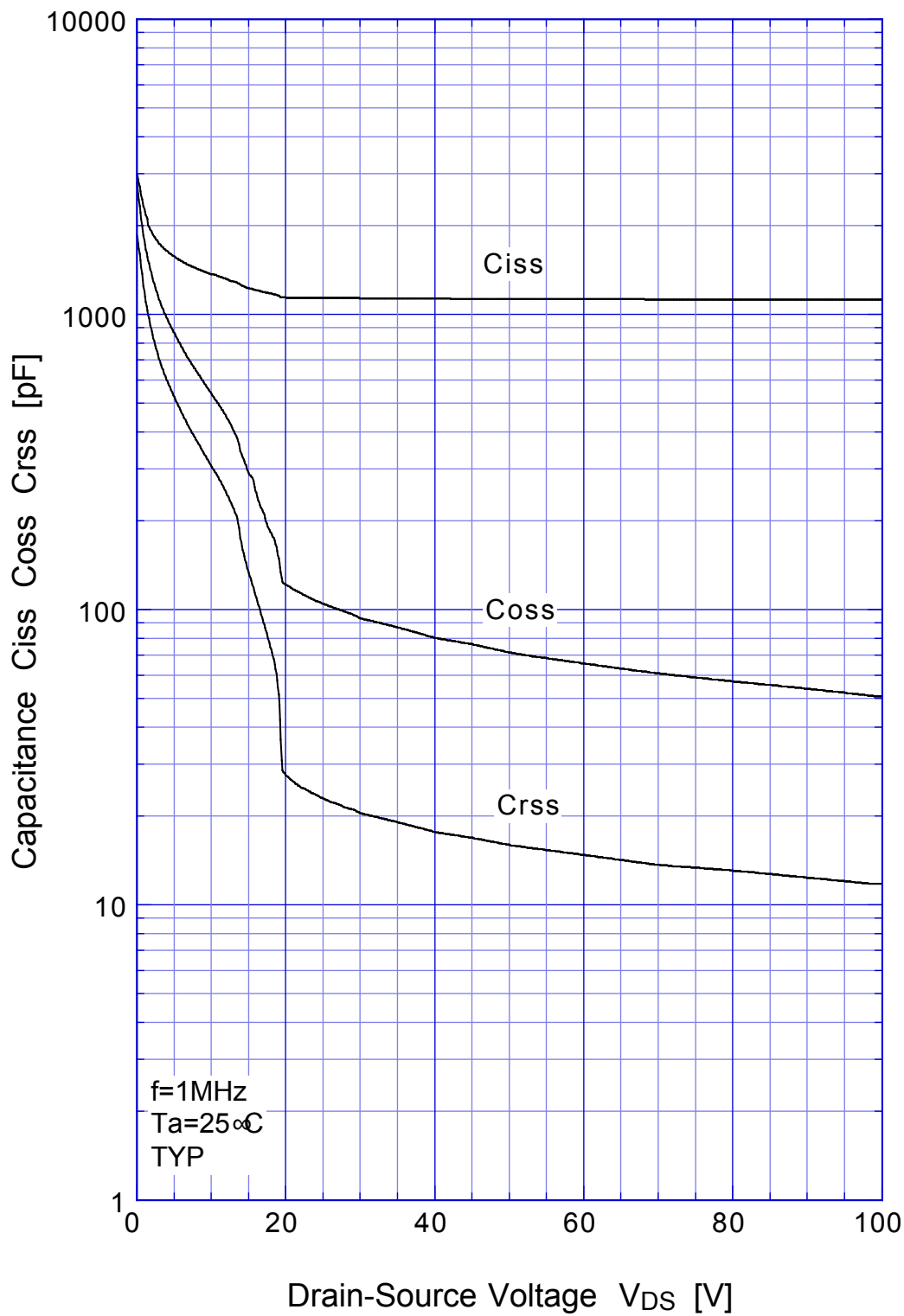
2SK2672 Transient Thermal Impedance



2SK2672 Single Avalanche Energy Derating

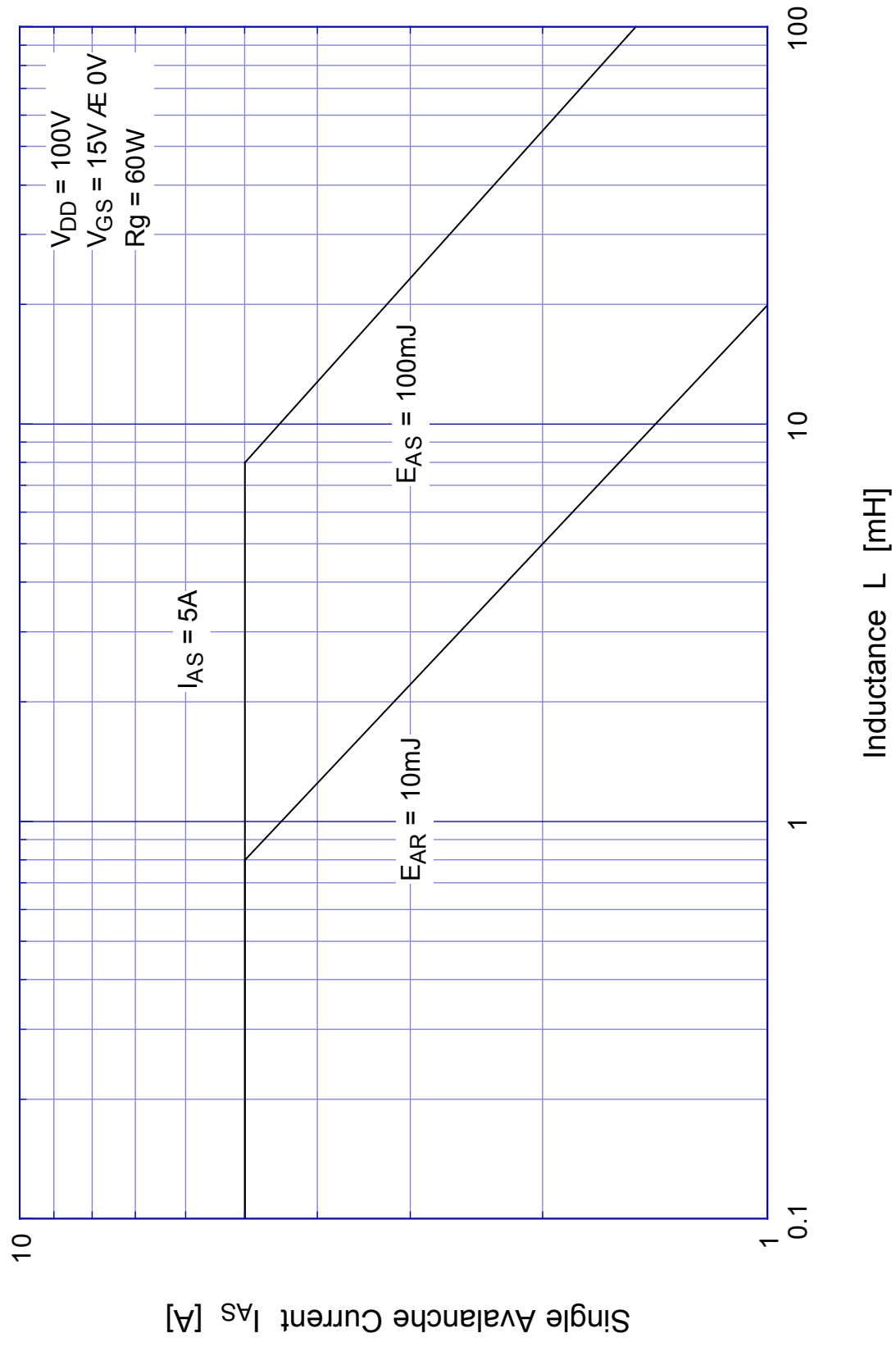


2SK2672 Capacitance



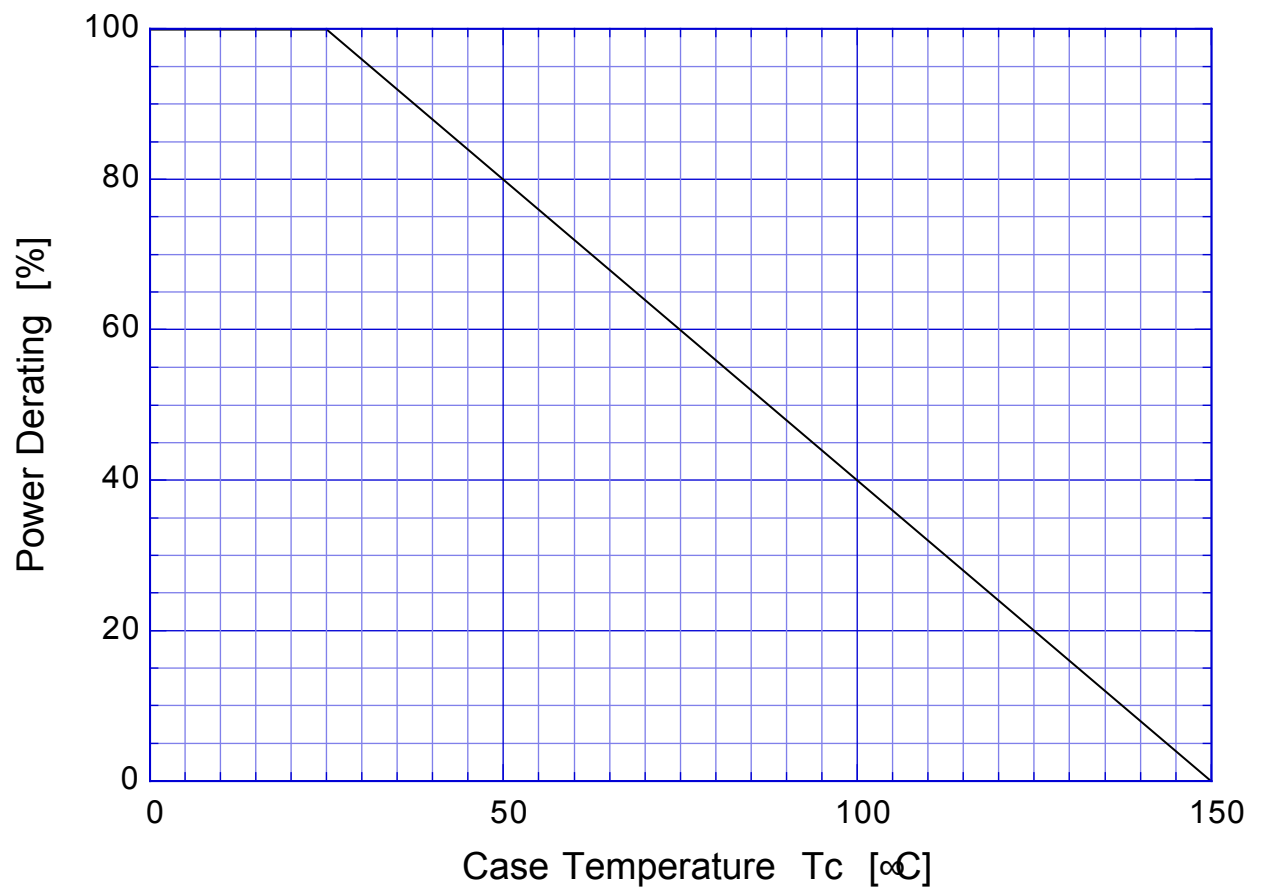
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Single Avalanche Current - Inductive Load



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Power Derating



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Gate Charge Characteristics

